

NONLINEAR EFFECTS IN CW MODE-LOCKED SOLID-STATE LASERS WITH SEMICONDUCTOR SATURABLE ABSORBERS

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Abstract

The influence of nonlinear properties of semiconductor saturable absorbers on ultrashort pulse generation was investigated. It was shown, that linewidth enhancement, quadratic and linear ac Stark effect contribute essentially to the mode locking in cw solid-state lasers, that can increase the pulse stability, decrease pulse duration and reduce the mode locking threshold.

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1 Introduction

Recently, a considerable progress has been made in self-starting femtosecond lasers using semiconductor structures [1]. This allows to generate the pulses with duration of 5.5 fs directly from the resonator [2]. Laser systems with semiconductor modulators combine the advantages of the Kerr-lens mode locking system with self-starting operation and alignment insensitivity [3]. The most striking feature of semiconductor absorbers used in the experiments is a long (~ 100 fs $\div$ 10 ps) recovery time as compare with pulse duration. To explain such extremely short pulse generation the soliton mode-locking mechanism was proposed [4]. This mechanism involves the stabilization of

the Schrödinger soliton against cw laser continuum (noise) due to noise decay within the positive net-gain window, which is much longer than the pulse. However, not only semiconductor loss saturation, but also others nonlinear effects, in particular, absorption linewidth enhancement and ac Stark-effect neglected in the above theory can contribute to mode-locking and produce a strong self-amplitude modulation (see, for example [5]) and thus should be taken into account.

Here we present simple models for mode-locking due to the linear and quadratic Stark shift of the excitonic resonance and ultra-short pulse stabilization due to linewidth enhancement.

2 Ultrashort pulse generation in the presence of the absorption linewidth enhancement

It is known, that the semiconductor structures used as passive modulators possess an extremely high nonlinearity, which depends on the carrier density and, consequently, on the pulse energy (see, for example, [6]). This produces a strong energy-dependent self-phase modulation (SPM), which is proportional to loss coefficient. The corresponding coefficient of proportionality (Henry's factor) is about $-3 \div -8$ [7, 8].

The aim of this section is to describe an ultrashort pulse generation in cw solid-state laser in the presence of fast nonlinear refraction in active medium and carriers density dependent SPM in semiconductor absorber. As we shall demonstrate later on, the last factor transforms the pulse characteristics essentially and can stabilize an ultrashort pulse against automodulational instability. In addition, it will be shown that the absorption linewidth enhancement produces a negative feedback, which leads to multistable operation. One should note the difference from an existing theory [4], where quasi-Schrödinger laser soliton was studied.

2.1 Model

Based on the self-consistent field theory [9] and taking into account the gain, the saturable loss in semiconductor, frequency filtering, the GVD and the SPM we arrive to the master equation:

$$\frac{\partial a(k, t)}{\partial k} = \alpha - \Gamma[\exp[-\frac{\epsilon}{U_a}] + i\chi(\exp[-\frac{\epsilon}{U_a}] - 1)](1 + \frac{\partial}{\partial t})^{-1} + \quad (1)$$

$$\left[\frac{1}{(1 + \frac{\partial}{\partial t})} - 1\right] - l + id\frac{\partial^2}{\partial t^2} - i\beta |a(k, t)|^2 + i\phi a(k, t),$$

where $a(k, t)$ is the field, k is the transit number, t is the local time, α is the dynamically saturated gain, l is the linear loss, Γ is the initial saturable loss, ϵ is the instant pulse energy flux, U_a is the loss saturation energy flux, ϕ is the phase delay after the full round trip, d is the GVD coefficient, β is the SPM coefficient of active medium, χ is the Henry's factor. The term in the straight parentheses with the derivation stands for the frequency filtering. All times are normalized to the inverse filter bandwidth t_f and the equal bandwidths for the loss and frequency filter are assumed for the sake of simplicity. The gain dispersion is neglected.

An expansion of eq. (1) into the series in energy and account for the dynamical loss and gain saturation by the pulse energy

$\epsilon = \int_{t_0}^t |a(k, t')|^2 dt'$ (t_0 is the time moment corresponding to the pulse peak) yields:

$$\begin{aligned} \frac{\partial a(k, t)}{\partial k} = & \alpha_0(1 - \tau\epsilon + \frac{(\tau\epsilon)^2}{2}) - l - \gamma_0 - \\ & \gamma_0(1 + i\chi)(\frac{\epsilon^2}{2} - \epsilon) - (1 - \gamma_0(1 - \epsilon))\frac{\partial}{\partial t} + \\ & (1 - \gamma_0)\frac{\partial^2}{\partial t^2} + id\frac{\partial^2}{\partial t^2} - i\chi\gamma_0\epsilon\frac{\partial}{\partial t} + \\ & i\phi - ip|a(k, t)|^2 a(k, t), \end{aligned} \quad (2)$$

where α_0 and γ_0 are the saturated gain and the saturated loss at the pulse peak, respectively. In eq. (2) the pulse energy flux is normalized to the saturation energy flux of the absorber U_a , τ is the ratio of the loss saturation energy flux to the gain saturation energy flux (with account for the mode cross-sections at the absorber and at the active medium), $p = \frac{\beta U_a}{t_f}$.

A soliton-like solution of eq. (2) is sought in the form

$$a(k, t) = a_0 \text{sech}^{1+i\psi}[(t - k\delta)/t_p] \exp[i\omega(t - k\delta)], \quad (3)$$

where a_0 is the pulse amplitude, δ is the round-trip delay so that $t_0 = k\delta$, t_p is the pulse duration, ω is the frequency shift from the center of the transmission band of the filter, ψ is the pulse chirp. Substitution of the expression (3) into (2) gives the set of six algebraic equations. Solution of this set gives explicit expressions for six unknown a_0 , t_p , ψ , ω , δ and ϕ , however too clumsy to write them out here.

To relate the parameters of our model to those controllable in experiment we have to recalculate the saturated loss at pulse the peak γ_0 with respect to the initial saturable loss Γ : $\gamma_0 = e^{-E/2}$, assuming that the loss recovery time is much shorter than the cavity period T_{cav} and much longer than the pulse duration. Here $E = \int_{-\infty}^{\infty} |a|^2 dt$ is the full pulse energy. Although in the typical femtosecond lasers the gain saturation energy is much bigger than the loss saturation energy (in our calculations $\tau = 0.0015$, which corresponds to the absorption saturation flux of $100 \mu J/cm^2$, Ti:sapphire active medium and the beam radii of 30 and $106 \mu m$ at the active crystal and at the absorber, respectively), our calculations have shown, that the balance between these two factors noticeably affects ultrashort pulse parameters. The saturated gain α_0 can be found as follow: $\alpha_0 = \alpha_m \frac{1-\exp(-U)}{1-\exp(-U-\tau E)} \exp(-\tau E/2)$, where U is the pump power normalized to $\frac{\sigma_{14} T_{cav}}{h\nu}$, $h\nu$ is the pump photon energy, σ_{14} is the absorption cross section of the active medium, α_m is the gain at full inversion. This equation gives an additional relation for determining unknown system's parameter α_0 .

2.2 Ultra-short pulse characteristics and pulse stability

Our analysis showed, that in the presence of SPM in the active medium ($p \neq 0$ in eq. (2)), there exist two distinctly different pulse-like solutions of eq. (2) (parameters of this solution are presented by curves 1 of Figs. 1 - 3, where the solid lines denote a stable solution). The difference in the nature of this two solutions is explained by contribution from the different pulse-forming mechanisms: 1) the Schrödinger soliton mechanism, producing chirp-free pulse with zero frequency shift and 2) "laser" (dissipative) mechanism, producing essentially chirped quasi-soliton with non-zero frequency shift (curves 1 of Fig. 2). Both solutions have a minimum in duration for a certain pump power and GVD (curves 1 of Fig. 3) and nearly linear dependence of the pulse energy on the pump power.

Even a small energy-dependent nonlinear refraction ($\chi \neq 0$ in eq. (2)) «mixes» these two states, so that the chirp compensation is possible only for relatively large pump (Fig. 1, curves 2, 3) and for the shortest pulse the chirp remains uncompensated (Fig. 3, curves 2, 3). The features in the behavior of the pulse parameters in the presence of the linewidth enhancement are the broadening of the pump power region where an ultrashort pulse generation is possible (the growth of the maximal allowable pump power) and the increase of the Stokes shift of the pulse carrier frequency. The last factor produces a negative feedback due to the shift of the pulse spectrum from the gain band that decreases the pulse energy for large pump powers and broadens

the region of the pulse existence.

Now we have to investigate the stability of the solution obtained. The stability against small perturbations of the pulse parameters (i.e. amplitude, duration, frequency shift, chirp and energy) is considered. Substituting a perturbed solution (3) into eq. (2) and expanding it into the time series we get an equations set for the evolution of the pulse parameters:

$$\frac{da_0}{dk} = a_0[\alpha_0 - \gamma_0 - l - \omega^2(1 - \gamma_0) - v(1 - \gamma_0 - d\psi)], \quad (4)$$

$$\frac{d\omega}{dk} = a_0^2[\gamma_0(\chi - \omega - \psi - \chi\omega\psi) + \alpha_0 a_0^2 \psi \tau + 2v\omega(\gamma\psi^2 + \gamma_0 - \psi^2 - 1)], \quad (5)$$

$$\frac{dv}{dk} = a_0^4(\gamma_0 - \alpha_0 \tau^2) + 2a_0^2 \gamma_0 v(\chi\psi - 1) + 2v^2(3d\psi + \psi^2 + \gamma_0 - \gamma_0\psi - 1), \quad (6)$$

$$\begin{aligned} \frac{d\psi}{dk} = & -2a_0^2(\gamma_0\chi + p + \gamma_0\chi\psi^2) + \frac{a_0^4}{v}(\gamma_0\chi - \gamma_0\psi + \alpha_0\tau^2\chi) + \\ & 2v(\gamma_0\psi^2 + \psi\gamma_0 - 2d\psi^2 - \psi^2 - 2d), \end{aligned} \quad (7)$$

where $v = \frac{1}{t_p^2}$.

To obtain the condition for the pulse stability against energy perturbation we followed the scheme presented in [10]: integration of eq. (2) and summing up with its complex conjugate gives the energy conservation law. From this integral of motion the condition for the decay of the perturbation of the pulse energy follows:

$$\begin{aligned} & -\alpha_0 \tau e^{\frac{\tau E}{2}}(1 + e^{-\tau E}) + l + (1 + e^{-E}) - \\ & \frac{2\sqrt{v}}{3}(1 - \gamma_0)(1 + \psi^2 + 3\omega^2/v) - \frac{2}{3}\gamma_0 a_0^2(\chi\psi - 1) < 0 \end{aligned} \quad (8)$$

Here we assumed that the loss and the gain saturation obey the exponential law, which is the case for quasi-two level system with a relaxation time much longer than the pulse duration. Our stability analysis is a modification of the analysis of stability against laser noise presented in [10] with energy perturbation playing the role of gain saturation by the noise continuum.

Negative real part of the Jacobean of the eqs. set (4 - 8) is the condition for the pulse stability. It is seen from eqs. (4) and (8), that the frequency

shift, chirp and spectral filtering (forth term in eq. (8)) stabilize the pulse against energy and amplitude perturbations, the «slow» (first term in eq. (5) and second term in eq. (7)) and the «fast» (first term in eq. (7)) SPM stabilize the pulse against frequency and chirp perturbations. This stabilization is provided by negative feedback due to pulse chirping and frequency shift in the presence of finite absorption and filter bandwidths.

Condition (8) is the condition of the pulse stability against laser noise generated within the frame of the pulse and it should be completed by the stability analysis against the noise generated behind the pulse within the window of the positive net-gain. As was shown in [11], the main stabilizing factor in this case is the difference in the group velocities of the pulse and the noise. The delay of the noise with respect to the positive net-gain window produces an additional loss for it and, consequently, stabilizes the pulse. A corresponding mathematical formulation for this condition leads to evolutionary equation for cw- noise with intensity N assuming that the noise consists of spontaneous spikes with durations much longer than t_f :

$$\frac{dN(k, t)}{dk} = \left\{ \alpha_0 e^{-\tau E/2} - l - V - \delta \frac{\partial V}{\partial t} \right\} N(k, t), \quad (9)$$

where $V = (1 + (e^{-E} - 1)e^{-t/T_a})$ is “ potential” created by the pulse, the derivative describes the time shift of the noise with respect to the pulse. From this the condition for the decay of the noise energy results:

$$\alpha_0 e^{-\frac{\tau E}{2}} - l - e^{-E} + \frac{\delta}{T_a} (1 - e^{-E}) < 0. \quad (10)$$

The solutions of eq. (2) which is stable against parameter perturbations (automodulational stability) are shown in Figs. 1 - 3 by solid lines. It should be noted, that the soliton mode locking mechanism does not work over the full region of pulse existence, which is evidenced by essentially non-zero chirp of the pulse and one may conclude that the pulse stability is provided here by interplay between others lasing factors . As is seen from Figs. 1 - 3, a relatively large nonlinear refraction in semiconductor causes a bistable operation: there appear two stable solutions (curves 4), that exist simultaneously for some pump power range around 4 W. One of these solutions has a smaller chirp, larger Stokes shift, shorter duration and lower energy.

Negative feedback due to absorption linewidth enhancement stabilizes the pulse against pulse energy perturbation. The mechanism of such stabilization is explained by dependence of the pulse frequency shift on the pulse energy: the increase of the pulse energy produces a bigger frequency shift (curves 4, 5 of Fig. 2 b), which makes the pulse amplification inefficient due to the bad

overlap of the pulse and gain spectra. This prevents from further growth of the pulse energy; the opposite situation prevents from the decrease of the pulse energy.

Fig. 4 demonstrates the regions of the pulse existence A , automodulational stability B , stability against laser noise C and full pulse stability D . It is seen, that in the absence of linewidth enhancement there is no automodulational stability due to insufficiency of the negative feedback in the system (Fig. 4, a). The increase of the negative linewidth enhancement factor increases the threshold of the pulse generation due to nonlinear loss produced by pulse frequency shift, but the automodulational stability region arises due to the action of «slow» SPM in the semiconductor (Fig. 4, b). This is accompanied by the pulse shortening down to shortest possible duration t_f and the full pulse stabilization for some pump and GVD (dark region D of Fig. 4, b).

Thus, we have demonstrated the influence of absorption linewidth enhancement in semiconductor on the ultrashort pulse characteristics in solid-state lasers. The linewidth enhancement introduces a negative feedback that stabilizes the pulse. The region of the pulse stability is much wider in this case than in the case of the soliton stabilization. At low pump powers and low negative GVD a dramatic growth of the pulse duration is observed. Bistable operation for large pump powers is possible. The advantage of mode-locking mechanism described above is the operation without Kerr-lensing, which is very attractive for diode-pumped cavity alignment insensitive system with large mode cross section.

3 Ultrashort pulse generation in the presence of the quadratic ac Stark effect

An absorption linewidth enhancement is not a single nonlinear mechanism in semiconductors that may contribute to mode-locking. Estimations show that the Stark shift of the excitonic resonance in the presence of strong laser field can be a strong pulse-shaping factor, too [5, 12]. Furthermore, an experimental utilization of the Stark effect due to external modulation was successfully used for active mode-locking of diode-pumped Nd: YAG laser [13].

3.1 Model

Quadratic ac Stark shift $\Delta\omega$ that is due to the influence of nonresonant transitions on excitonic resonance is proportional to the polarizability difference

between ground and excited states $\Delta\alpha$ [14]: $\Delta\omega = |\Delta\alpha| \times |E|^2/\hbar$, where E is the field strength. The typical values of $|\Delta\alpha|$ for semiconductors are of order $10^{-19} \div 10^{-21} \text{ cm}^3$ [15], that corresponds to the Stark shift coefficient $\zeta = 8\pi|\Delta\alpha|/(n\hbar) = (10^5 \div 10^3)/n \text{ cm}^2 \text{ J}^{-1}$, where n is the index of refraction. Neglecting the population of higher energy levels of semiconductor and under weak exciton-exciton, exciton-phonon bound approximation, one can describe the interaction between laser field and quantum-confined absorber by the generalized two-level model [14]. The evolution of the off-diagonal element of the density matrix Π and the population difference between ground and excited states Ξ obey the differential equation set:

$$\begin{aligned} \frac{d\Pi}{dt} + \left[\frac{1}{t_a} - i(\omega_l - \omega_a - \Delta\omega)\right]\Pi &= \frac{i}{\hbar}\wp\Xi, \\ \frac{d\Xi}{dt} + \frac{\Xi - \Xi_0}{T} &= -\frac{4}{\hbar}\text{Im}(\Pi\wp^*), \end{aligned} \quad (11)$$

where t_a is the inverse bandwidth of the absorption line, ω_a is the resonance frequency, ω_l is the field carrier frequency, $\wp$ is the matrix element of the interaction, Ξ_0 is the equilibrium population difference. The Stark shift which is possible only in generalized two-level model, in quasi-monochromatic approximation, i. e. under neglecting the cross-modulation between different pulse spectral components, is proportional to $\varsigma |a(t)|^2$.

In the noncoherent approach, the evolution of the complex field $a(t)$ in the laser system containing the gain medium, saturable absorber, frequency filter and dispersive element obeys nonlinear operator's equation: $a^{k+1}(t) = \tilde{\Gamma}\tilde{G}\tilde{D}a^k(t)$, where k is the round trip number, t is the local time. The Lorentzian gain band action is described by $\tilde{G} = \exp(\frac{\alpha L_g}{1 + L_g t_g \frac{\partial}{\partial t}})$, $L_g = \frac{1}{1 + i(\omega_l - \omega_g)t_g}$ where ω_g is the gain resonance, t_g is the inverse gain bandwidth (for Cr: forsterite chosen for our calculations, $t_g = 20 \text{ fs}$), α is the saturated gain. $\tilde{D} = \exp(id \frac{\partial^2}{\partial t^2})$ is the second-order GVD group velocity dispersion operator, where d is the dispersion amount introduced by the prism pair. From eq. (11) one derives an operator accounting for the effects of saturable absorption and nonlinear contribution due to Stark-effect

$$\Gamma = \exp \frac{\int_{t_0}^t \gamma L_a \exp[-\text{Re}(L_a) \int |a(t')|^2 \exp(-\frac{t-t'}{T}) dt'/U_a]}{1 + L_a t_a \frac{\partial}{\partial t}} - l, \text{ where}$$

$$L_a = \frac{1}{1 + i[\omega_l - (\omega_a + \mu|a(t)|^2)]t_a}, \quad U_a \text{ is the saturation energy, } \gamma \text{ is the saturated loss at the moment } t_0 \text{ corresponding to the pulse peak, } l \text{ is the linear loss.}$$

 The integral in Γ accounts for the ordinary slow saturable absorption with recovery time T . Here we used the normalization as in previous section, so that for PbS – based modulator with $U_a = 390 \mu\text{J}/\text{cm}^2$ [16] $\mu = \zeta U_a = 13$.

An expansion of laser equation into series on t , local field energy and intensity, provided that the pulse duration is much shorter than T , gives the laser dynamical equation similar to the generalized Landau-Ginzburg equation:

$$\begin{aligned} \frac{\partial a(k, t)}{\partial k} = & [c_1 + ic_2 \frac{\partial}{\partial t} + (c_3 + ic_4) \frac{\partial^2}{\partial t^2} + \\ & (c_5 + ic_6) |a(k, t)|^2 + (c_7 + ic_8) \epsilon + \\ & (c_9 + ic_{10}) \frac{\epsilon^2}{2} + (c_{11} + ic_{12}) \epsilon \frac{\partial}{\partial t}] a(k, t), \end{aligned} \quad (12)$$

where $\epsilon = \int_{t_0}^t |a(k, t')|^2 dt'$, $c_1 = \alpha J_g - \gamma J_a - l$, $c_2 = 2\alpha \Omega J_g^2 - 2\gamma \omega \vartheta^2 J_a^2$, $c_3 = (1 - 3\Omega^2) J_g^3 - \gamma(1 - 3\omega^2 \vartheta^2) J_a^3 \vartheta^2$, $c_4 = \alpha(\Omega^3 - 3\Omega) J_g^3 - \gamma(\omega^3 \vartheta^3 - 3\omega \vartheta) J_a^3 \vartheta^2 + d$, $c_5 = -2\gamma \omega \vartheta \mu H_a$, $c_6 = -\gamma \mu(1 - \omega^2 \vartheta^2) H_a$, $c_7 = \gamma J_g^2$, $c_8 = -\gamma \omega \vartheta J_a^2$, $c_9 = -\gamma J_a^3$, $c_{10} = \gamma \omega \vartheta J_a^3$, $c_{11} = -\gamma(1 - \vartheta^2 \omega^2) J_a^3 \vartheta$, $c_{12} = 2\omega \gamma \vartheta^2 J_a^3$, $J_a = \frac{1}{1 + \omega^2 \vartheta^2}$, $J_g = \frac{1}{1 + \Omega^2}$, $H_a = \frac{1}{(1 - \omega^2 \vartheta^2)^2 + 4\omega^2 \vartheta^2}$, $\omega = \omega_l - \omega_a$, $\Omega = \omega_l - \omega_g$, $\vartheta = t_a/t_g$. We normalized all times to t_g , frequencies to t_g^{-1} , dispersion coefficient to t_g^2 , the intensity to $\frac{U_a}{t_g}$.

3.2 Stark induced mode locking

As one can see, Eq. (12) contains the term $-2\mu\gamma H_a \omega \vartheta |a(k, t)|^2 a(k, t)$, which is responsible for the fast saturable absorption at the below band-gap excitation with $\omega < 0$ (i. e. red shift of the pulse carrier frequency from the excitonic resonance). The shift ω is due to detuning between the gain and loss resonances ($\omega_g - \omega_a < 0$). The fast saturable absorber action is caused by the induced “pushing out” of the excitonic resonance from the red-shifted pulse spectrum due to power-dependent blue Stark shift. The corresponding saturation intensity is $I_s = [-2\mu\gamma H_a t_a (\omega_l - \omega_a)]^{-1}$. Our calculations showed, that the saturation intensity is close to the level, which is typical for Kerr-lens mode-locked lasers and is high enough to provide self-starting.

Eq. (12) has quasi-solution solution $a(k, t) = a_0 \text{sech}^{1+i\psi}[(t - k\delta)/t_p] e^{i\phi z}$, where the pulse parameters have the same meaning as in section 2.2. The duration and frequency shift for chirp-free solution and necessary GVD are presented in Fig. 5. It is seen, that the minimal pulse durations (close to the limit defined by t_g) are provided by $(\omega_a - \omega_g)t_g = 0.3 \div 0.7$. The growth of the initial unsaturated loss Γ shortens the pulse duration (curve 2 in compare with 1). The minimum of pulse duration in $\omega_a - \omega_g$ approximately coincides with the minimum of I_s . Using of smaller U_a increases the duration (curve 3)

because the absorber operates in the regime of strong saturation. A stronger saturation results in an additional blue shift of the pulse with respect to the gain resonance (curve 3 of Fig. 5, b) (for the explanation of the mechanism of this shift see [17]), which does not favor the Stark induced mode locking. As is seen from eq. (12), ac Stark effect contributes both to SPM-term c_6 and GVD-term c_4 , which modifies the amount of GVD from prism pair necessary for chirp compensation (Fig. 5, c).

Using the absorber with narrower band in compare with gain band (curve 4) reduces the region of $\omega_g - \omega_a$, where chirp-free pulses exist because the pulse spectrum and excitonic line do not overlap. However, in this case the generation of the chirped pulses with duration close to t_g is possible (Fig. 6). The larger τ requires positive dispersion d for pulse existence (curve 2 in compare to 1), which is explained by the change of the sign of self-phase modulation coefficient in c_6 . It should be noted, however, that for the case of large τ it is necessary to account for the coherent nature of pulse-semiconductor interaction (here such effects as self-induced transparency are possible [18]), which indeed transforms mode-locking dynamics essentially, but falls out the frame of the present model.

The predicted dependence of the pulse parameters on the frequency shift from excitonic resonance is confirmed by experimental results presented in [12]. Here, in particular, there is no ultrashort pulse generation at no shift from excitonic resonance, a relatively small Stokes shift of the laser frequency from the excitonic resonance caused fs-pulse operation, while the increase of the Stokes shift brings the pulse duration into picosecond region. Our conclusions that the strong saturation of semiconductor absorption does not favor the Stark-induced amplitude modulation also corroborates with experimental results [5].

In order to perform the stability analysis we calculated the net-gain Σ behind the pulse tail. Evidently, the pulse would be unstable, if $\Sigma > 0$ for some frequency ω_n from the noise spectral region. Fig. 7 shows Σ for five selected noise frequencies ($\Delta = \omega_n - \omega_l$). It is seen that the decrease of Γ (Fig. 7, a in compare with b), decrease of U_a (Fig. 7, c in compare with Fig. 7, b) or growth of ϑ (Fig. 7, d) destabilizes the chirp-free pulse, but the suitable detuning between absorber and gain resonances $\omega_a - \omega_g$ allows for stable ultra-short pulse generation with duration much shorter than the absorber recovery time.

So, the quadratic Stark effect in semiconductor absorbers causes a stable ultrashort pulse generation in case of relatively small absorption saturation and below band-gap excitation. The generation of chirp-free pulses with the duration close to the theoretical minimum is possible.

Next section is devoted to the case of the strong absorber saturation which

is the typical situation for real antiresonant Fabry-Perot saturable absorber mirrors [4] and requires some modifications to be introduced in our model.

4 Ultrashort pulse generation in the presence of linear ac Stark effect

Here we shall demonstrate that the linear Stark effect at near-resonance interaction with semiconductor absorber can efficiently reduce the threshold of ultrashort pulse generation with the durations close to shortest possible. We present a theory for the formation of “weak-nonlinear” soliton with GVD balanced by SPM which is proportional rather the amplitude than the intensity of the field.

As is known [19], an optical Stark effect in semiconductors with reduced dimension is described in frame of “dressed-exciton” model [19, 20]. In this model the shift of excitonic resonance originates from the mixing of “field - matter” states. At below/above band-gap excitation a blue/red shift is observed (in the latter case the driving field falls into the absorption band of semiconductor which complicates an experimental observation of red shift), a precise coincidence between driving frequency and excitation resonance causes the splitting of resonance. The magnitude of the Stark shift is $\sqrt{\omega^2 + \varsigma |a|^2}$, where ω is the mismatch from resonance, a is the field, ς is the Stark shift coefficient (i. g. for GaAs/AlGaAs quantum well $\varsigma = 4 \times 10^{16} \text{ Hz} \cdot \text{cm}^2/\text{J}$ [21]). As was shown in [19, 13], the Stark shift produces almost noninertial amplitude modulation which may be used in ultrafast optical modulators.

4.1 Model

To describe the Stark shift of excitonic resonance at near-resonance interaction ($\omega \rightarrow 0$) with semiconductor absorber we adopted the following approximations: i) an excitonic bond has a Lorentzian profile, ii) the exciton-exciton bond is weak and therefore neglected, and iii) the field is quasi-monochromatic. For saturation flux of absorber we used $U_a = 100 \mu\text{J}/\text{cm}^2$, the relaxation time was much longer than the pulse duration. With the above assumptions, an operator for the interaction of the field with excitonic resonance is (see section 3.1):

$$\Gamma = - \frac{L_a \exp[-\text{Re} L_a \int_{-\infty}^t |a(t')|^2 dt'/U_a]}{1 + L_a t_a \frac{\partial}{\partial t}} \quad (13)$$

where $L_a = \frac{1}{1+i\kappa t_a |a(t)|}$ is the saturable loss, $\kappa = \sqrt{\zeta}$, t_a is the inverse absorption bandwidth, t is the local time.

Real semiconductor saturable absorber mirrors (SESAM's) operate in the condition of strong saturation [22], and one may therefore neglect the dynamical saturation and introduce a saturated by the full pulse energy loss γ :

$$\gamma = \frac{\Gamma}{1 + \text{Re} L_a \int_{-\infty}^{\infty} |a(t)|^2 dt / U_a}.$$

Thus, the basic pulse shaping mechanism here is that of soliton formation with the SPM balanced by the GVD, but the SPM now has two components, cubic in field (Kerr-nonlinearity in active medium) and quadratic in field (Stark-shift induced nonlinearity in semiconductor), the latter essentially transforming the nature and parameters of the pulse.

Expansion of eq. (11) into the power series in local time t and field a and retaining the terms up to the 2nd order yields:

$$\begin{aligned} \frac{\partial a(t, k)}{\partial k} = & [\alpha - \gamma - l + i\varphi] a(t, k) + \\ & \left[(\alpha - \gamma + id) \frac{\partial^2}{\partial t^2} \right] a(t, k) \mp \\ & [i\gamma |a| + (\gamma - ip) |a|^2] a(t, k), \end{aligned} \quad (14)$$

where k is round-trip number, α is the saturated gain, l is the linear loss, φ is the phase delay, d is the GVD amount, p is coefficient of Kerr-nonlinearity $\beta = \frac{2\pi n_2 z}{\lambda n}$ normalized to $t_a^2 \zeta$ (n_2 and n are nonlinear and linear refraction indices an active medium, z is the length of active medium, λ is the generation wavelength), the signs “−” and “+” correspond to below and above band-gap excitation. The saturated gain α is calculated through the gain at full inversion as

$$\alpha = \alpha_m \frac{1 - \exp(-U)}{1 - \exp(-U - \sigma \int_{-\infty}^{\infty} |a|^2 dt)} \exp(-\tau \int_{-\infty}^{\infty} |a|^2 dt / 2), \text{ where } U \text{ is the pump photon}$$

flux, normalized to cavity period T_{cav} and absorption cross-section σ_{13} , $\tau^{-1} = U_g \zeta t_a$ is normalized energy flux of the gain saturation. In eq. (14) the time and intensity are normalized to t_a and $t_a^2 \zeta$, respectively. We assumed also that the gain line has the Lorentzian profile and inverse bandwidth is equal to that of semiconductor absorber t_a . For Cr: forsterite laser ($t_a = 20$ fs) where an ultrashort pulse generation using the bleaching of excitation resonance in PbS quantum dots has been reported [12] with our normalizations and 3-mm long crystal the parameters τ and p are 0.01 and 0.1, respectively.

It is seen from eq. (14), that the Stark shift of excitonic resonance which may be understand as pulse-induced “pushing-out” of absorption band form

the pulse spectral profile introduces nonlinear (quadratic) phase modulation as well as fast saturable loss proportional to intensity. The sign of SPM in absorber coincides with that produced by Kerr-nonlinearity in active medium for the above band-gap excitation and is opposite for the below band-gap excitation.

In the general solution for eq. (14) is unknown, so we shall consider two limiting cases of eq. (14): i) weak generation field and ii) strong generation field. In the first case one may neglect the cubic in field term:

$$\begin{aligned} \frac{\partial a}{\partial k} = & [\alpha - \gamma - l + i\varphi] a + \\ & \left[(\alpha - \gamma + id) \frac{\partial^2}{\partial t^2} \right] a \mp \\ & i\gamma |a| a. \end{aligned} \quad (15)$$

In the second case one may neglect the quadratic in field term:

$$\begin{aligned} \frac{\partial a}{\partial k} = & [\alpha - \gamma - l + i\varphi] a + \\ & \left[(\alpha - \gamma + id) \frac{\partial^2}{\partial t^2} \right] a + \\ & (\gamma - ip) |a|^2 a \end{aligned} \quad (16)$$

4.2 Non-Schrödinger soliton in a solid-state laser with semiconductor saturable absorber

Eq. (15), which is analogues to the Fisher-equation [23], has a quasi-soliton solution in the form:

$$a(t) = a_0 \operatorname{sech}^{2+i\psi}(t/t_p), \quad (17)$$

where the pulse amplitude a_0 , the chirp ψ and the duration t_p relate as follows:

$$\begin{aligned} \psi &= \frac{5d \pm \sqrt{25d^2 + 24(\alpha - \gamma)^2}}{2(\gamma - \alpha)}, \\ t_p &= \sqrt{\frac{2(\alpha - \gamma) - d\psi}{\alpha - \gamma - l}}, \\ a_0 &= \frac{5\psi [(\alpha - \gamma)^2 + d^2]}{\gamma t_p^2 (\gamma - \alpha)}, \end{aligned} \quad (18)$$

The signs “−” and “+” have the same meaning as in eq. (14).

Eq. (16) is the equation for laser Schrödinger soliton generated in the system with the gain, loss, Kerr-nonlinearity and GVD [24]. The solution for eq. (16) is

$$a(t) = a_0 \text{sech}^{1+i\psi}(t/t_p), \quad (19)$$

with

$$\begin{aligned} a_0 &= \sqrt{\frac{(\gamma - \alpha)(\psi^2 - 2) - 3d\psi}{\gamma t_p^2}}, \\ t_p &= \sqrt{\frac{(\gamma - \alpha)(\psi^2 - 1) - 2d\psi}{\gamma - \alpha + l}}, \\ \psi &= \frac{\{3[dp + \gamma(\gamma - \alpha)] + \sqrt{9[dp + \gamma(\gamma - \alpha)]^2 + 8[p(\gamma - \alpha) - \gamma d]^2}\}}{2[p(\gamma - \alpha) - \gamma d]}. \end{aligned} \quad (20)$$

Pulse duration and chirp vs GVD are presented in Figs. 8 and 9. Solid curves 1 and 2 correspond to the case of weak field and below and above band-gap excitation, respectively. Dashed lines correspond to the case of strong field.

From Fig. 9 (solid line 1 and dashed line) one may see that at below band-gap excitation the signs of the chirp produced by Stark-shift in semiconductor and Kerr-nonlinearity in active medium coincide. In the first limiting case this reduces the pulse duration in the region of negative GVD. Characteristic features of solution of the type (17) are that i) the pulse duration is close to the minimal possible t_a , and the necessary pump rates are much lower than for pure quasi-Schrödinger soliton, that ii) full chirp compensation due to GVD is impossible and that iii) the GVD range where the solution exists is much narrower than that one for quasi-Schrödinger soliton.

Solution (17) is transformed essentially in the case of the above band-gap excitation (curves 2 in Figs. 8 and 9): the chirp changes its sign according to “defocusing” action of SPM in semiconductor and reaches its minimum (along with the pulse duration) at some positive GVD; the GVD range where the solution exists narrows as compare to the previous case.

To check the correctness of the approximation of the general equation (14) by eq. (15) for weak-field limit we investigated the behavior of the parameters of quasi-soliton (17) in eq. (15) perturbed by cubic term. Substitution of (17) into (14) and expansion into the time series yields an algebraic equations set:

$$\begin{aligned}
2(\gamma - \alpha) + d\psi - (\gamma - \alpha + l)t_p^2 + \gamma a_0^2 t_p^2 &= 0, \\
-6(\gamma - \alpha) - 5d\psi + (\gamma - \alpha)\psi^2 - 2\gamma a_0^2 t_p^2 &= 0, \\
-12d + 4(\gamma - \alpha)\psi - 3d\psi^2 + (\gamma - \alpha)\psi^3 - 2a_0 t_p^2 \gamma - 2a_0^2 t_p^2 (2p + \psi\gamma) &= 0.
\end{aligned} \tag{21}$$

The pulse duration and the chirp obtained from these equations are presented by dotted lines in Figs. 8 and 9. It is seen, that for the weak-field approximation the cubic term is really just a perturbation and changes the solution only slightly. One can see also, that when the signs of SPM in active medium and in semiconductor coincide (above band-gap excitation), the decrease of pulse duration is observed, while for the opposite signs (below band-gap excitation) the duration increases.

Analysis of the pulse stability against perturbation of its parameters (amplitude, duration and chirp) and energy was performed as follows. Substituting expression (17) into eq. (14) and expanding it into the time series we arrive to the equations set for the pulse parameters evolution. As before (Sec. 2.2) the condition for the pulse stability against small parameters perturbations is the real part of Jacobean of the system to be nonpositive. After multiplying eq. (14) by complex-conjugate field, summing up with complex-conjugate expression and integrating over full time we get the conservation law for the pulse energy from which the condition for small energy perturbation evolution follows.

All solutions presented in Figs. 8 and 9 satisfy the above stability criterion. As analysis shows, the main destabilizing factor is $-d\psi$, however at small negative GVD it may be dominated by stabilizing factors (gain, loss, spectral filtering and saturable loss) thus making the stable ultrashort pulse generation possible.

In order to investigate the pulse characteristics in the intermediate region of field intensities we sought for the approximate solution of eq. (14) in the form

$$a(t) = a_0 \exp(-(t/t_p)^2 + i\psi t^2), \tag{22}$$

The pulse parameters are calculated then through the substitution of expression (22) into eq. (14), the expansion into the time series and solving the algebraic equations set for the unknowns a_0 , t_p , ψ . The first two relations read:

$$a_0 = \{4[d\gamma + (\alpha - \gamma)p + (l + \gamma - \alpha)t_p^2 p/2 + \tag{23}$$

$$t_p = \sqrt{\frac{2\psi t_p^2(\gamma(\alpha - \gamma) - dp) - d\gamma\psi^2 t_p^4}{- \gamma^2 t_p^2}} \cdot \sqrt{\frac{\alpha - \gamma - l - 2d\psi}{2\psi^2(\gamma - \alpha)}}.$$

The duration of the stable pulse vs pump power is presented in Fig. 10, where solid curves 1 and 2 correspond the below and above band-gap excitation, respectively, dashed line is the pulse duration for the case with no Stark-effect. It is seen, that for the case of the below band-gap excitation the contribution of quadratic SPM in semiconductor essentially reduces the pulse duration as compare to the case with no Stark-effect, so that one can achieve a short pulse generation (with duration of $100 \div 200$ fs) even at low pump powers (curve 1 and dashed curve). For the case of the above band-gap excitation an abrupt switch from ps- to fs-regime is observed at the pump-power for which the cubic nonlinearity begins to dominate over the quadratic one (compare this behavior with that described in [24]).

Thus, we demonstrated that the linear Stark-shift of excitonic resonance at near resonance interaction of ultrashort pulses with semiconductor saturable absorber in cw solid-state laser transforms the pulse characteristics essentially: due to formation of “weak-nonlinear” optical soliton. At low pump power and the below band-gap excitation a remarkable decrease of the pulse duration takes place, while at the above band-gap excitation a switch from ps- to fs-regime is observed.

5 Conclusions

Nonlinear properties of semiconductor saturable absorbers, such as linewidth enhancement, quadratic and linear ac Stark effect contribute essentially to the mode locking in cw solid-state lasers. The linewidth enhancement due to carrier density induced slow nonlinear refraction produces a negative feedback, which stabilizes ultrashort pulse against automodulational instabilities and expands the region of the pulse existence. Besides, this nonlinear factor can produce multistable lasing and switching to regime of the picosecond pulse generation.

At relatively small absorption saturation, the quadratic ac Stark shift of absorption line produces a fast saturable absorber action. The saturation intensity of this fast saturation is comparable to that of typical Kerr-lens mode locked lasers. For the case of strong absorption saturation the linear ac Stark effect produces a “weak-nonlinear” soliton at relatively small pulse intensities, that reduces the threshold of the ultrashort pulse formation.

The main advantages of lasing regimes described above are the operation without Kerr-lensing, which is very attractive for diode-pumped cavity alignment insensitive system with large mode cross section, the self-starting ability and the relatively small thresholds for fs-pulse generation.

6 References

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7 Figure captions

Fig. 1. Chirp ψ versus pump power for different linewidth enhancement factors: $\chi = 0$ (1), -0.005 (2), -0.05 (3), -2.5 (4). Every parameters set has two solutions. Stable solutions are plotted by solid lines. GVD coefficient is -360 fs^2 , $\Gamma = 0.05$, $l = 0.05$, $a_m = 1.5$, $p = 3$.

Fig. 2. Frequency shift ω versus pump power for different linewidth enhancement factors and GVD coefficients: $\chi = 0$ (1), -0.005 (2), -0.05 (3), -2.5 (4, 5); $d = -360 \text{ fs}^2$ (1 - 4), -90 fs^2 (5). Other parameters are as in Fig. 2. Stable solutions are plotted by solid lines. To better illustrate the behavior of the curves the plot is divided into parts *a* and *b*.

Fig. 3. Pulse duration t_p versus pump power for different linewidth enhancement factors and GVD coefficients: $\chi = 0$ (1), -0.005 (2), -0.05 (3), -2.5 (4, 5); $d = -360 \text{ fs}^2$ (1 - 4), -90 fs^2 (5). Other parameters are as in Fig. 2. Stable solutions are plotted by solid lines.

Fig. 4. Regions of pulse existence. (*A*) – region of instability, (*B*) – auto-modulational stability, (*C*) – stability against noise, (*D*) – automodulational and noise stability on the plane (GVD – pump power). $\chi = 0$ (*a*), -2.5 (*b*).

Fig. 5. Duration t_p (*a*), GVD amount d (*b*) and normalized frequency mismatch from excitonic resonance Ωt_g (*c*) for chirp-free solution versus normalized mismatch between gain and absorption resonances $(\omega_a - \omega_g) \times t_g$. $\chi = 13$ (1, 3, 4), 8 (2), $\Gamma = 0.05$ (1, 2), 0.1 (3, 4), $\vartheta = 1$ (1-3), 3 (4), $\alpha - r = 0.01$.

Fig. 6. Chirp ψ (*a*) and duration of the pulse t_p (*b*) versus GVD amount d . $\vartheta = 1$ (1), 30 (2), $(\omega_a - \omega_g) \times t_g = 0.5$ (1), 0.2 (2); $\chi = 13$, $\Gamma = 0.1$, $\alpha - r = 0.001$.

Fig. 7. Net-gain Σ behind the pulse tail for five selected noise frequencies $(\omega_n - \omega_l) \times t_g = 1$ (curve1), 0.5 (2), 0 (3), -0.5 (4), -1 (5). $\chi = 13$ (*a*, *c*, *d*), 8 (*b*), $\Gamma = 0.05$ (*a*, *b*), 0.1 (*c*, *d*), $\vartheta = 1$ (*a*, *b*, *c*), 3 (*d*).

Fig. 8. Duration of the stable pulse t_p versus GVD d . Curve 1 - pulse (17) at below band-gap excitation, curve 1 - pulse (17) at above band-gap excitation, dashed curve - pulse (19), dotted curves - pulse (17) as solution for eq. (15) perturbed by cubic nonlinearity. Pump power is 310 mW (solid and dotted curves) and 9.7 W (dashed curve), pump beam radius is $50 \text{ }\mu\text{m}$, $\alpha_m = 1$, $\Gamma = 0.1$, $l = 0.05$.

Fig. 9. Chirp ψ of the stable pulse versus GVD d . Curve 1 - pulse (17) at below band-gap excitation, curve 1 - pulse (17) at above band-gap excitation, dashed curve - pulse (19), dotted curves - pulse (17) as solution for eq. (15) perturbed by cubic nonlinearity. Other parameters are as in Fig. 8.

Fig. 10. Duration of the stable pulse (22) t_p versus pump power. Curve 1 - below band-gap excitation, curve 1 - above band-gap excitation, dotted curve - the case with no Stark-effect in semiconductor, $d = -15.6 \text{ fs}^2$ and other parameters as in Fig. 8.

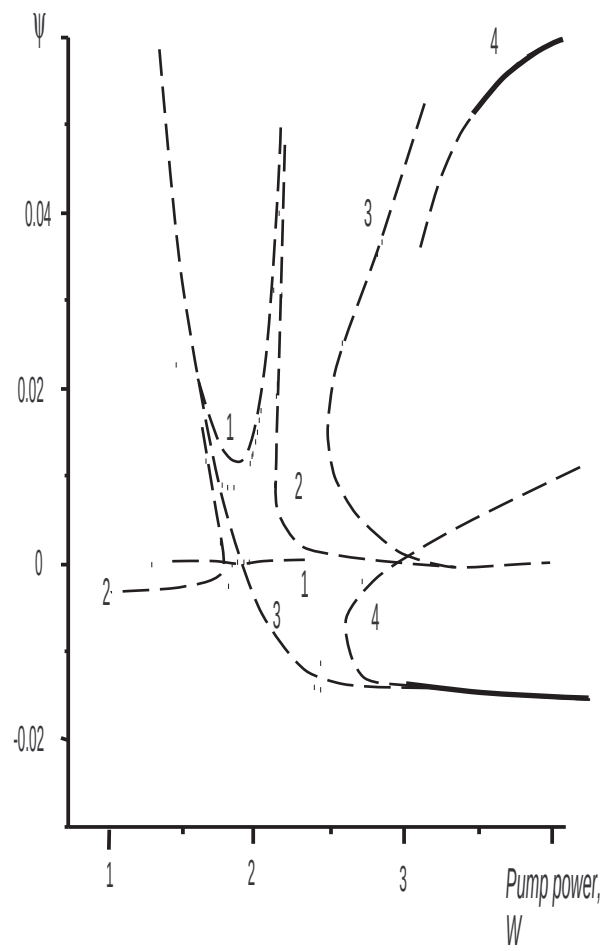


Figure 1: Chirp ψ versus pump power

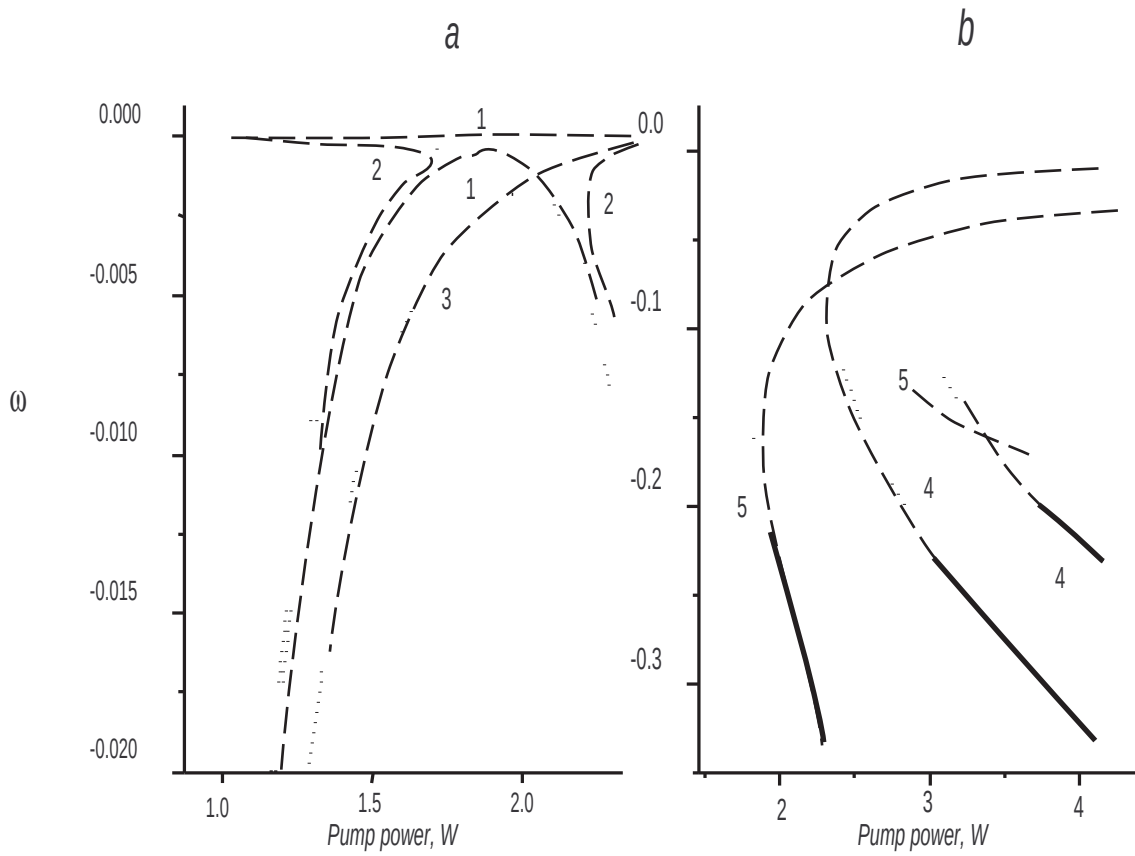


Figure 2: Frequency shift ω versus pump power

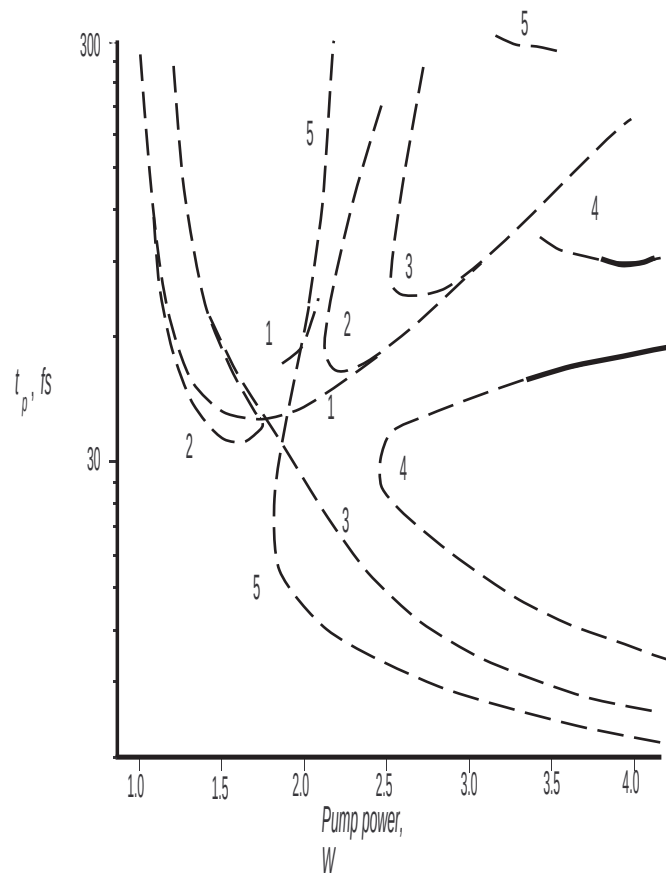


Figure 3: Pulse duration t_p versus pump power

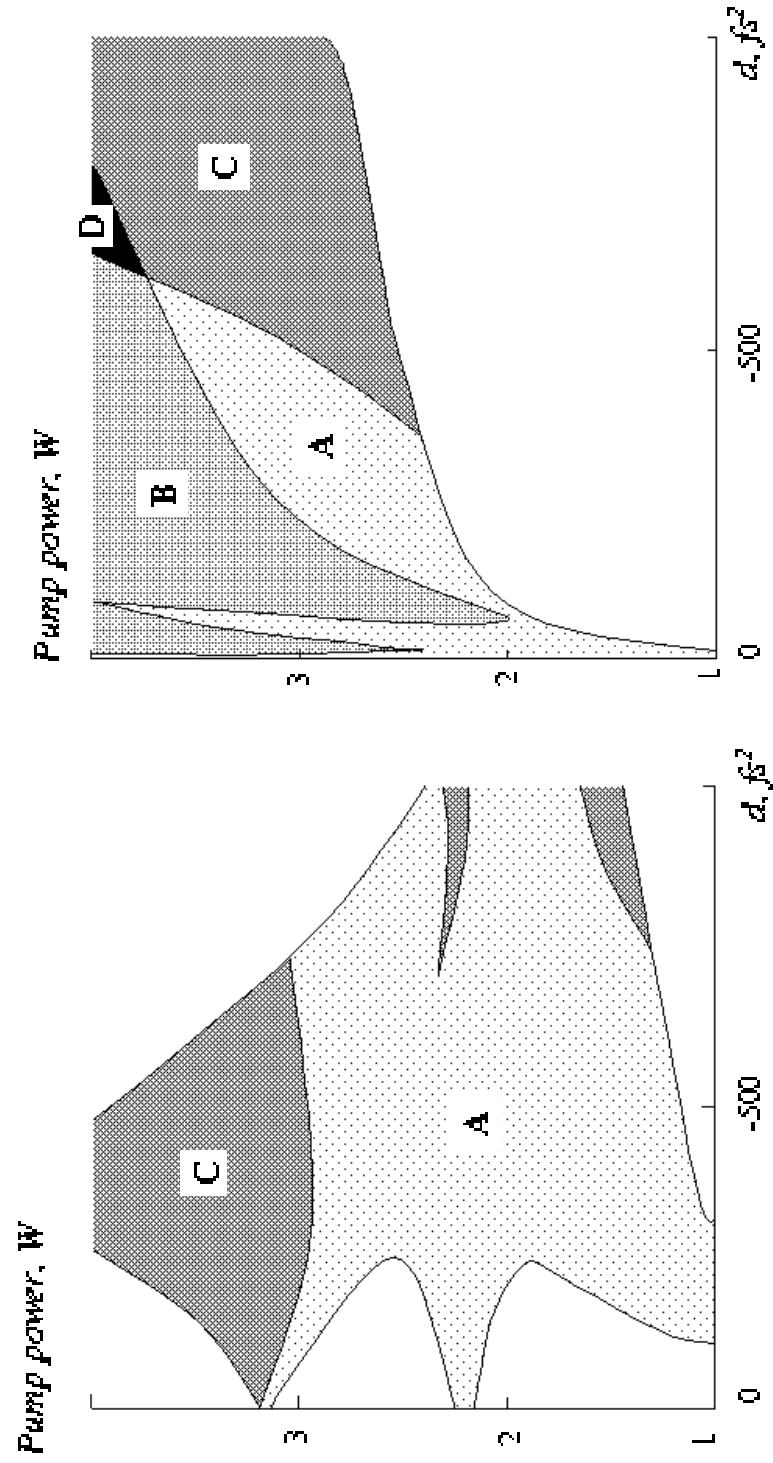


Figure 4: Regions of pulse existence

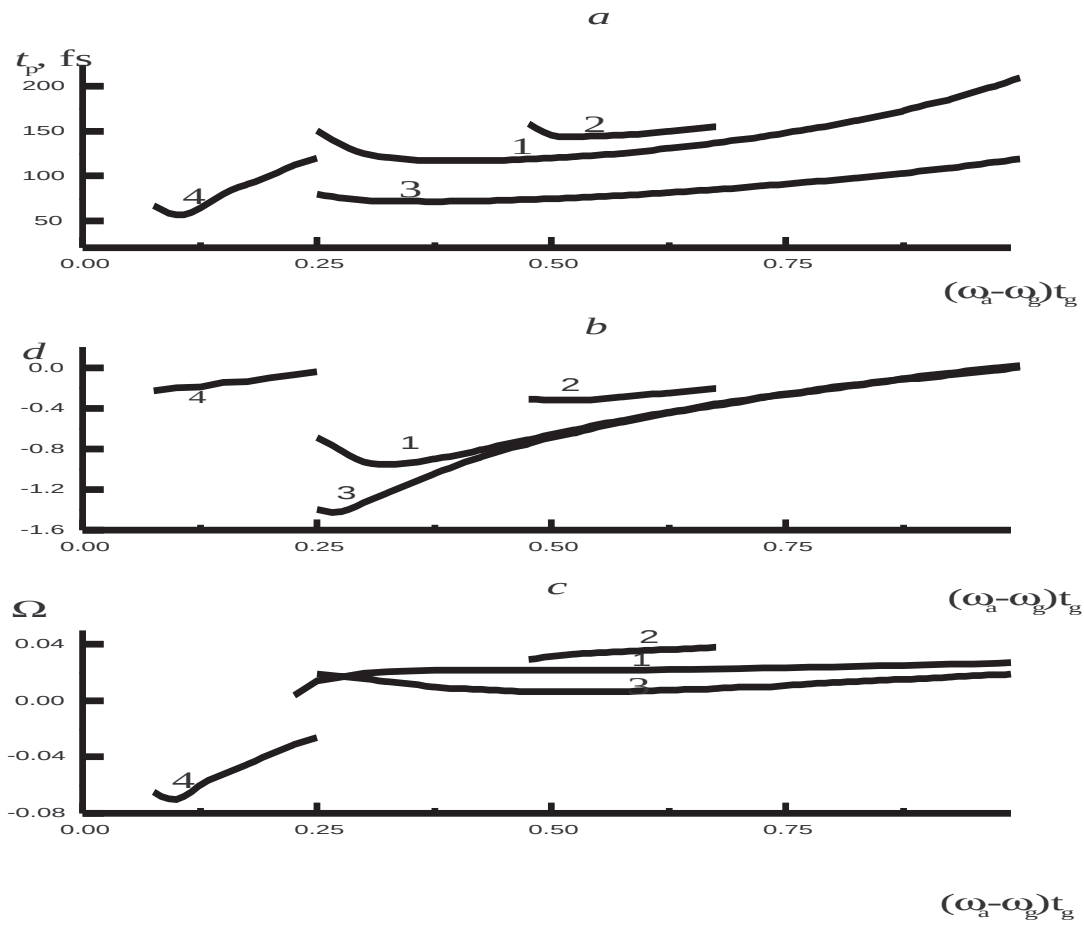


Figure 5: t_p (a), d (b) and Ωt_g (c) for chirp-free solution

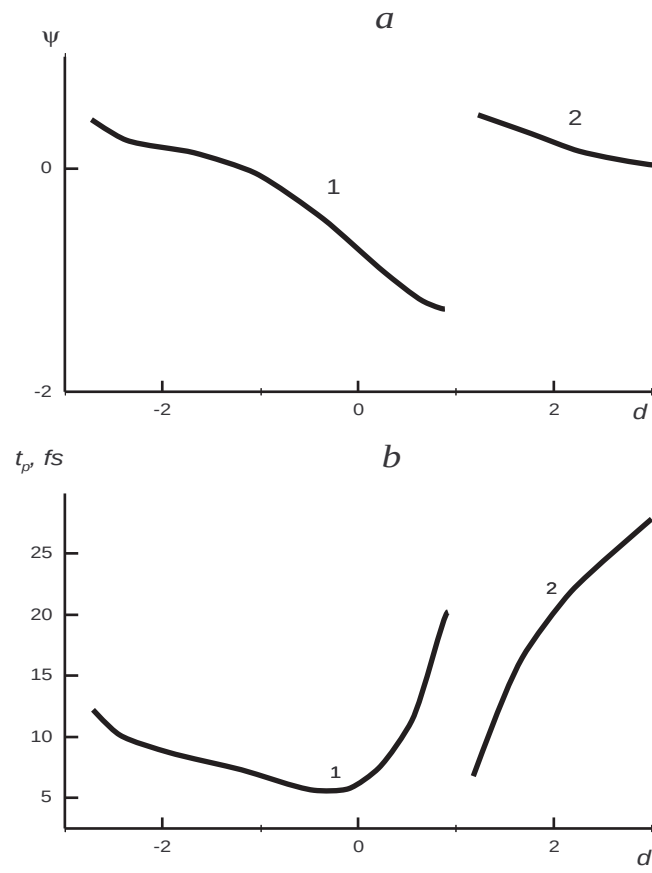


Figure 6: ψ (a) and t_p (b) versus d

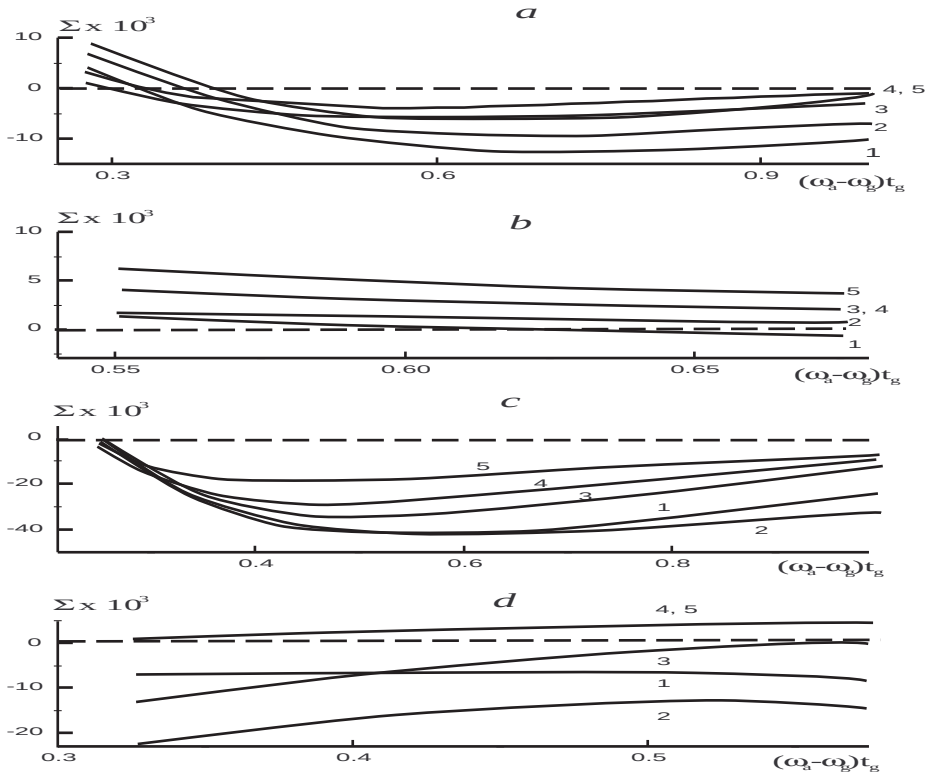


Figure 7: Net-gain Σ behind the pulse tail

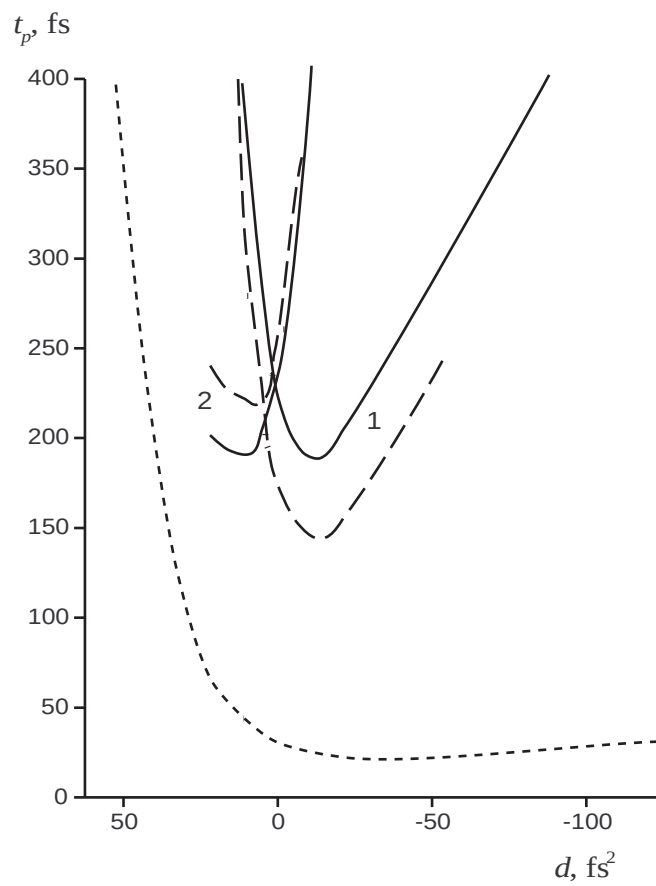


Figure 8: Duration of the stable pulse t_p versus GVD d

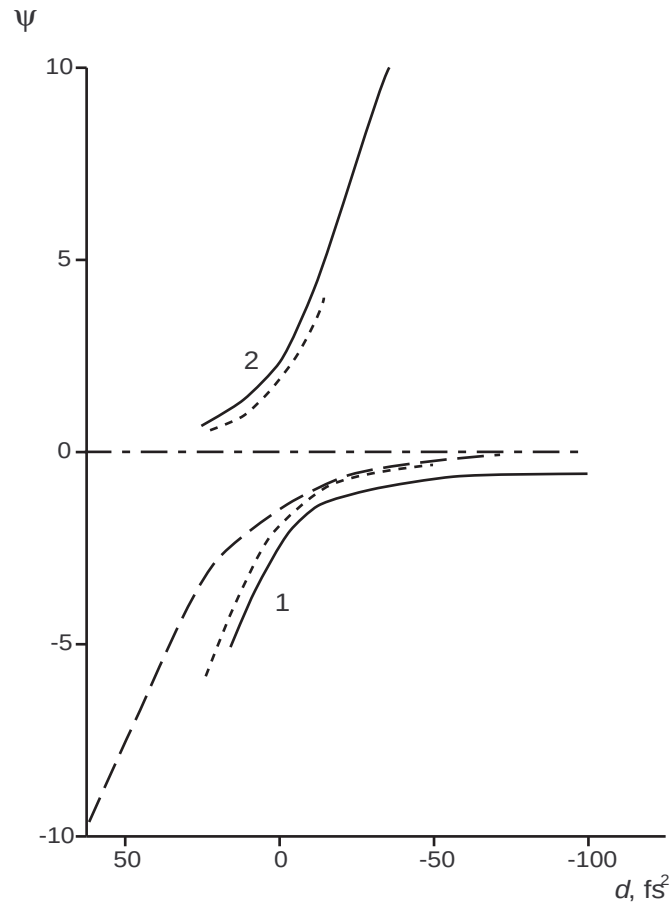


Figure 9: Chirp ψ of the stable pulse versus GVD d

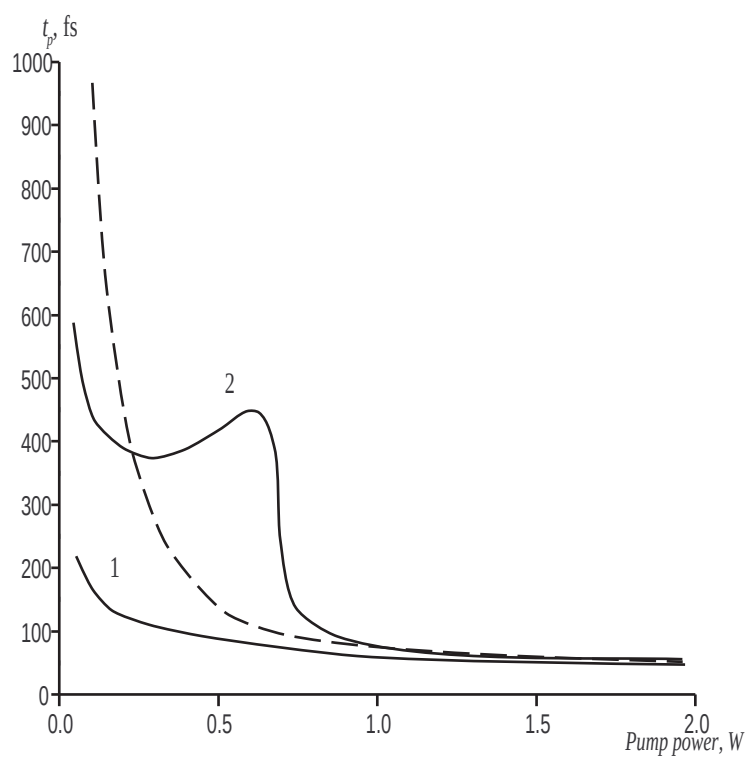


Figure 10: Duration of the stable pulse t_p versus pump power